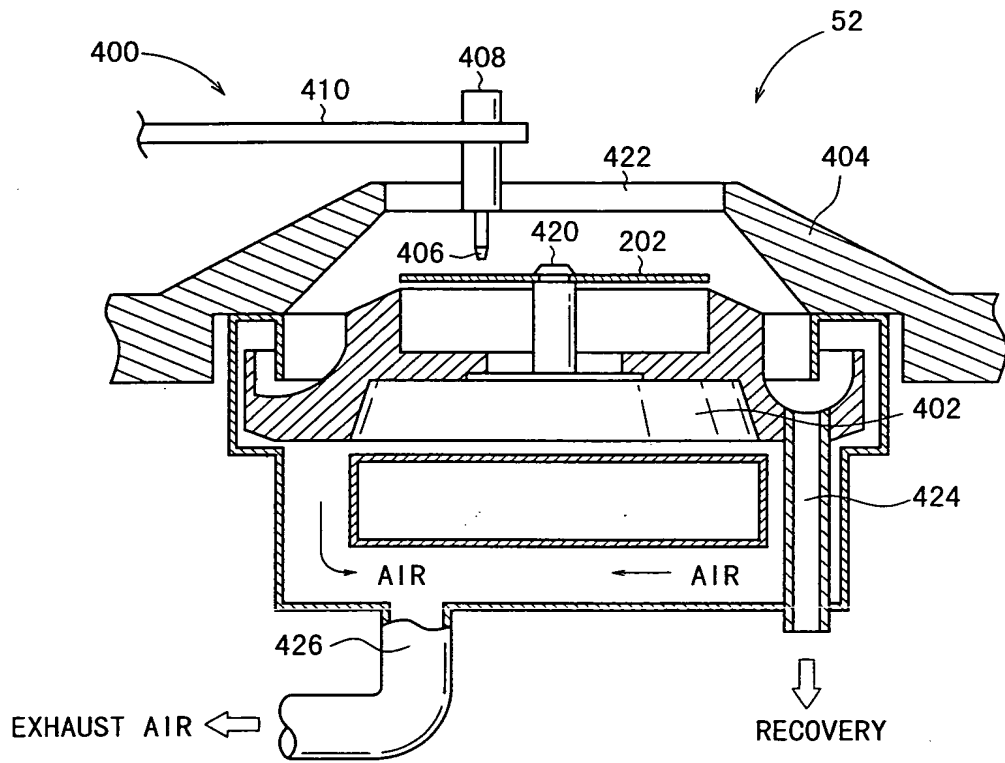


FIG. 2



RECOVERY

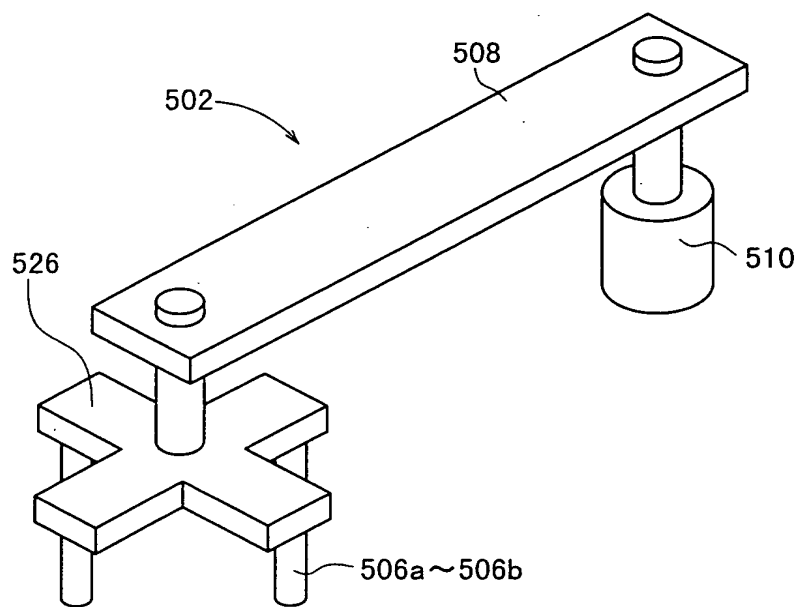


FIG. 6A

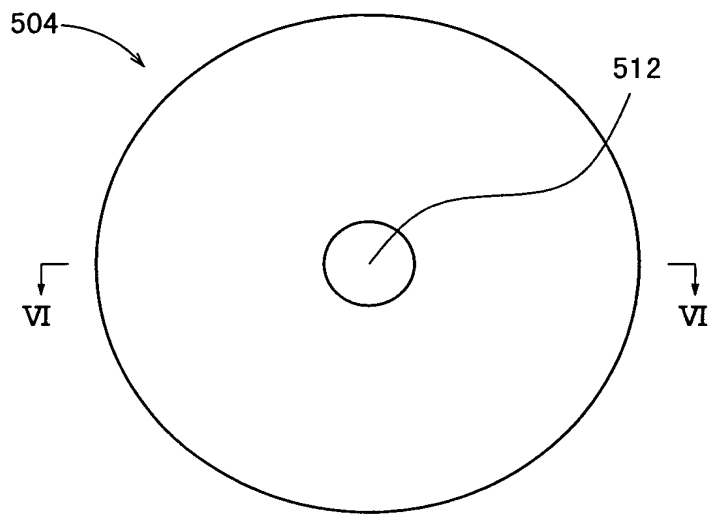


FIG. 6B



09634634.101000

FIG. 8A

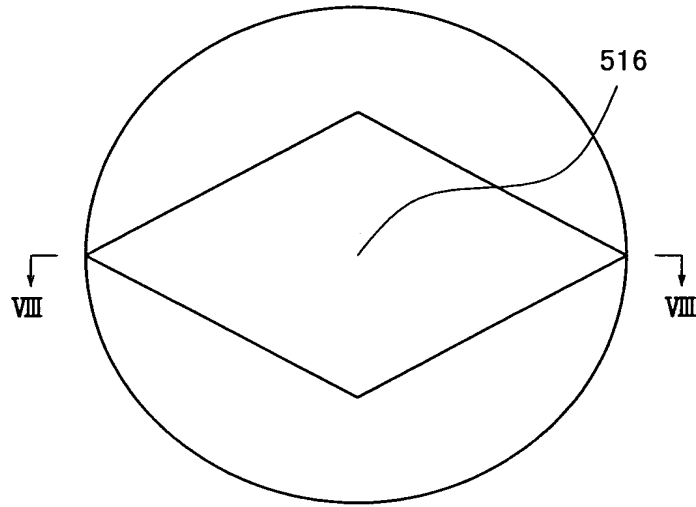


FIG. 8B



Figure 1 is a schematic diagram of a circular structure 520. Inside the large circle, there are four smaller circles of decreasing size arranged in a horizontal row. A label 520 with a leader line points to the largest of these smaller circles. On the left and right sides of the large circle, there are coordinate systems, each consisting of a downward-pointing arrow and the letter 'X'.

A diagram showing a large circle with a smaller circle inside it. A wavy line, labeled 522, originates from the center of the inner circle and extends towards the upper right edge of the large circle. On the left and right sides of the large circle, there are labels 'XI' with arrows pointing downwards.

FIG. 13

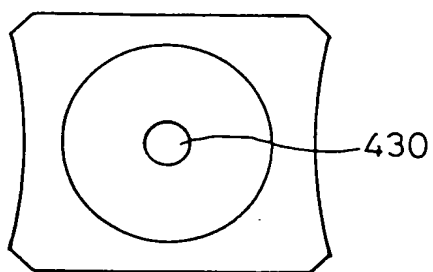


FIG. 14

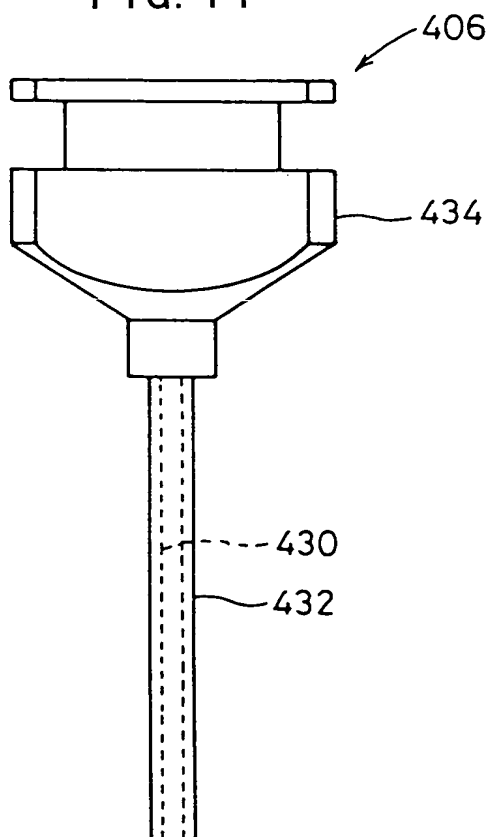
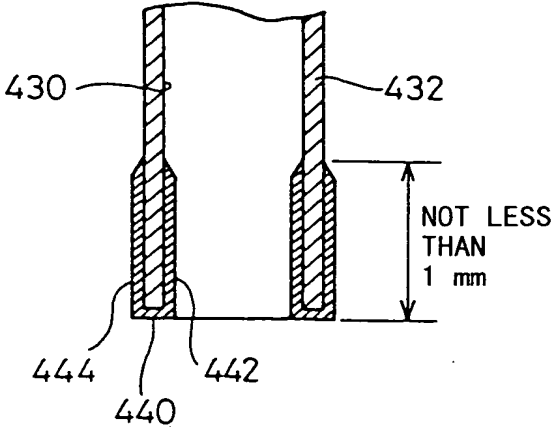
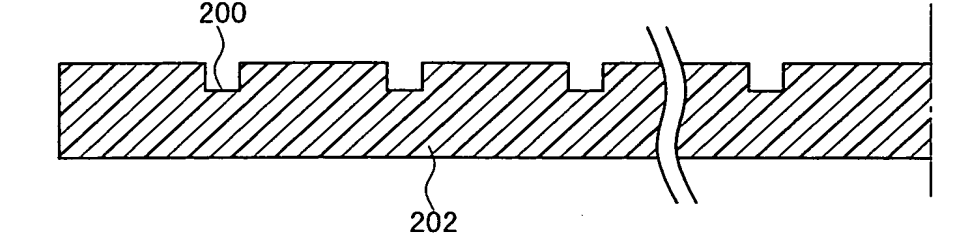
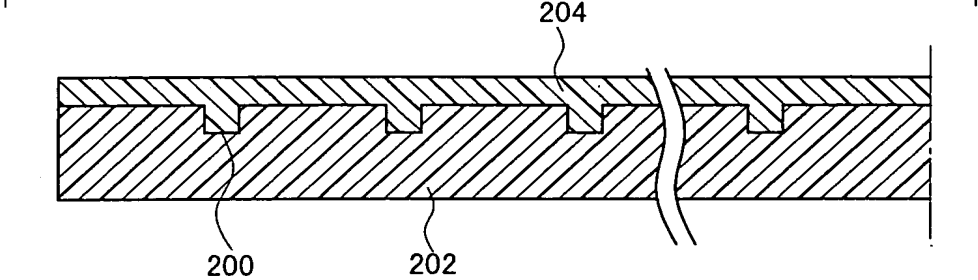


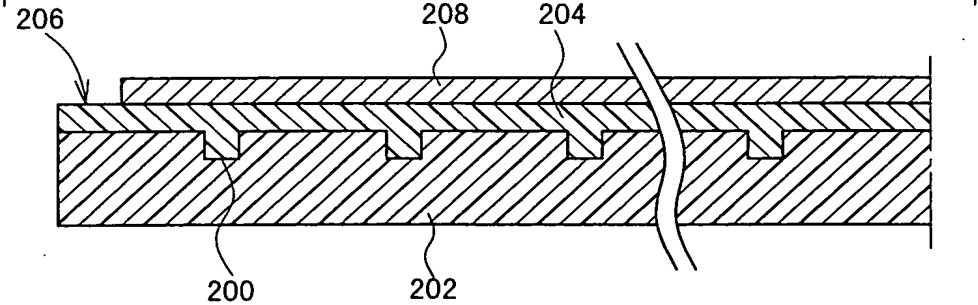
FIG. 15





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This cross-sectional view shows a substrate 200 with a series of rectangular trenches 202. A layer 204 is deposited over the substrate, filling the trenches. A top layer 206 is formed over the layer 204. A patterned layer 208 is on top of layer 206, with openings aligned with the trenches. A curved line indicates a cross-section through the device.

A cross-sectional view of a semiconductor device. It shows a substrate 200 with a top layer 202. A trench 204 is formed in the top layer 202, with its side walls labeled 210 and 208. A curved line labeled D indicates a boundary or interface within the device.

FIG. 19

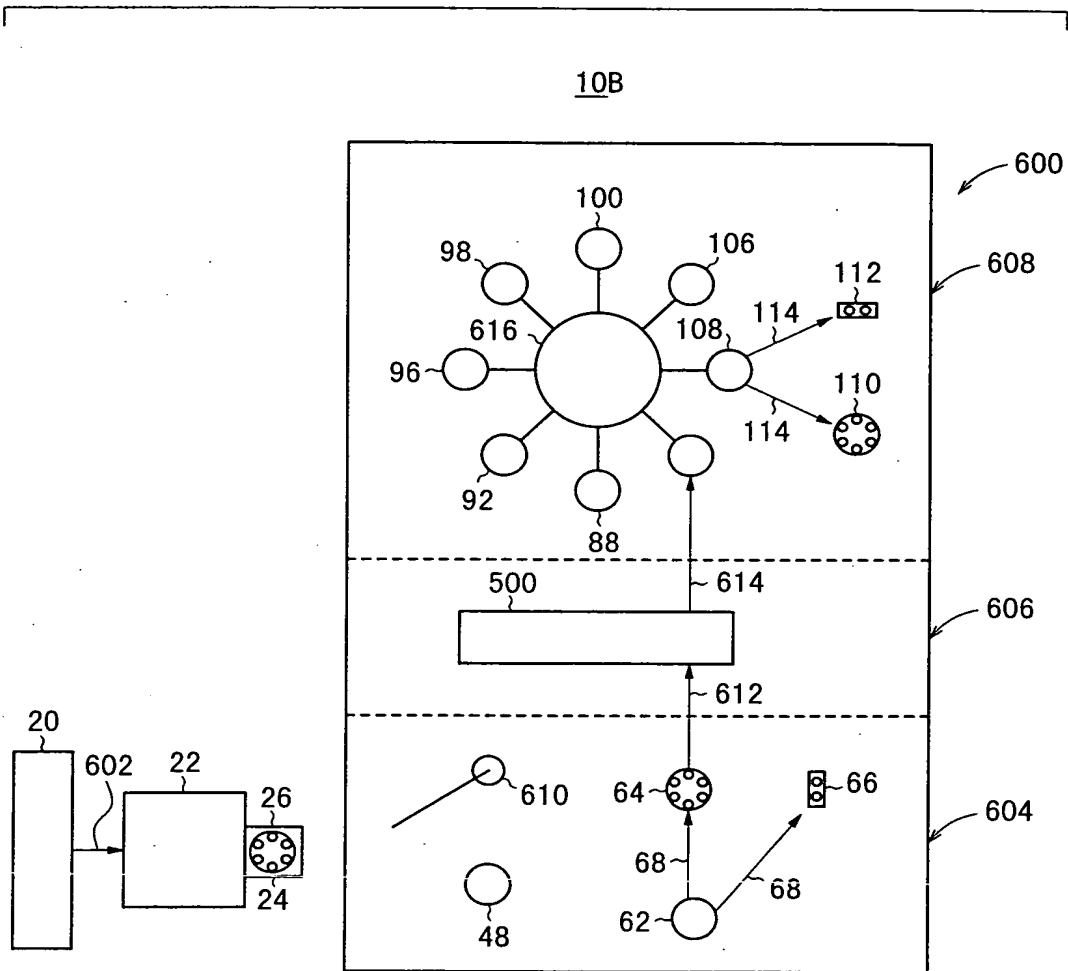


FIG. 22

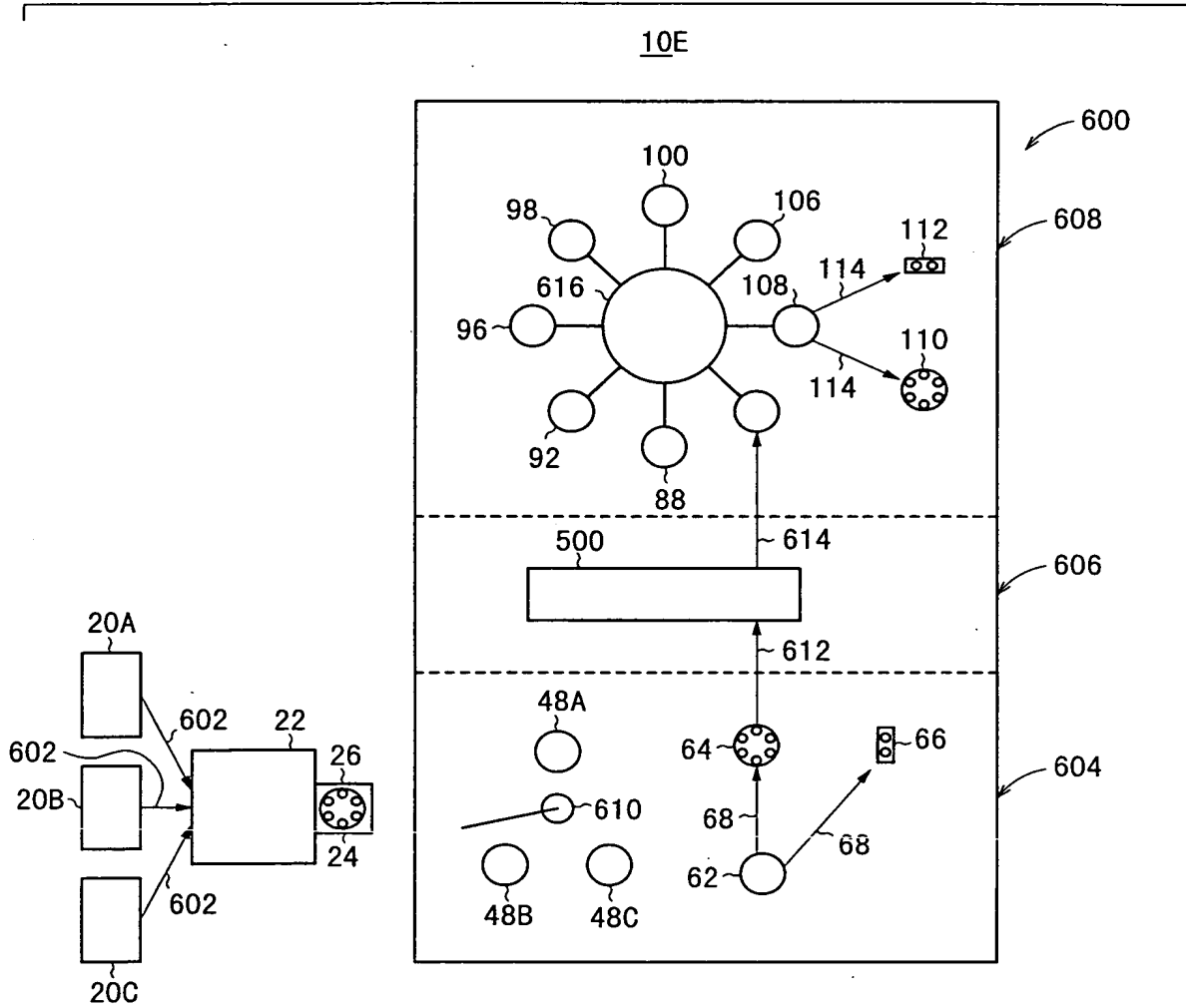
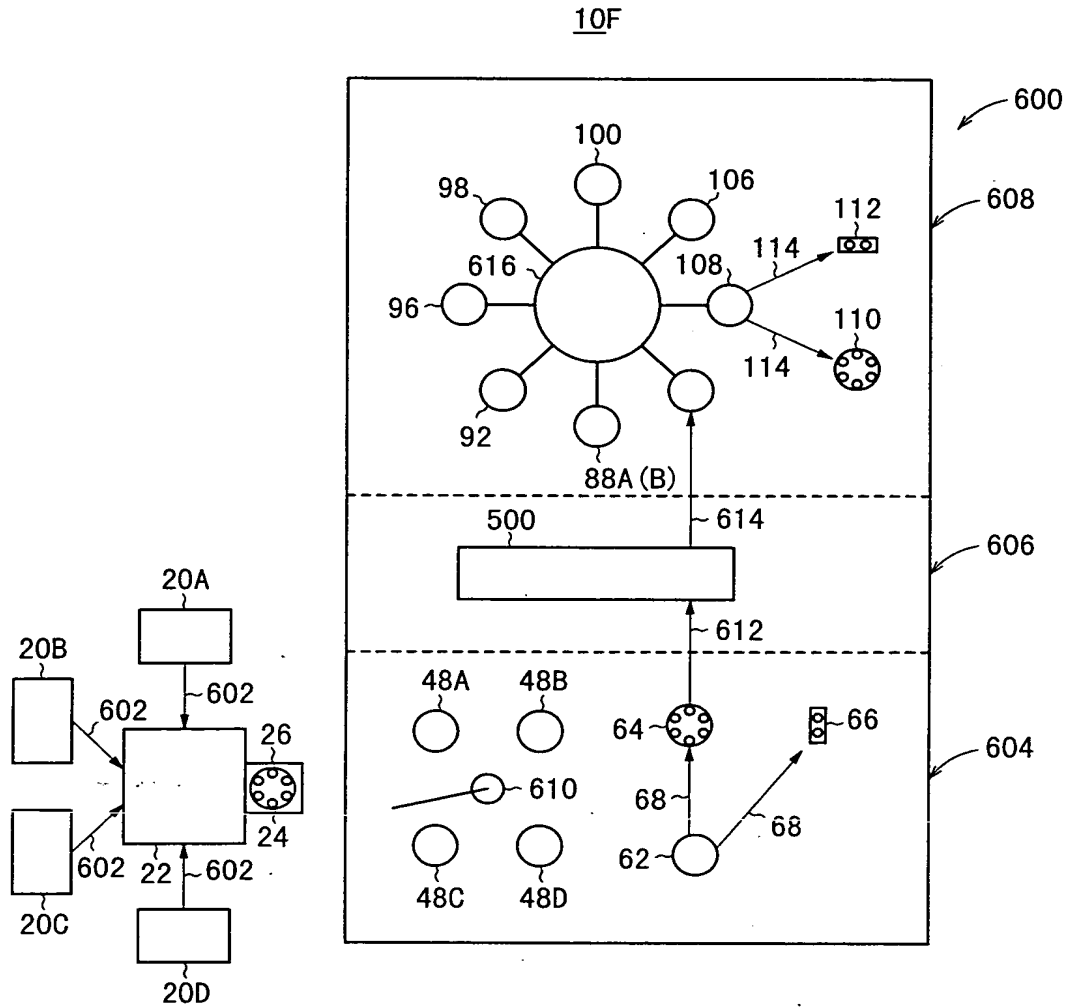


FIG. 23



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FIG. 24

